



YJM05GP06A

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-60 V
I_D	-5 A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	55 m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	70 m

General Description

Split gate trench MOSFET technology
Extremely low switching loss
Excellent stability and uniformity
Moisture Sensitivity Level 1



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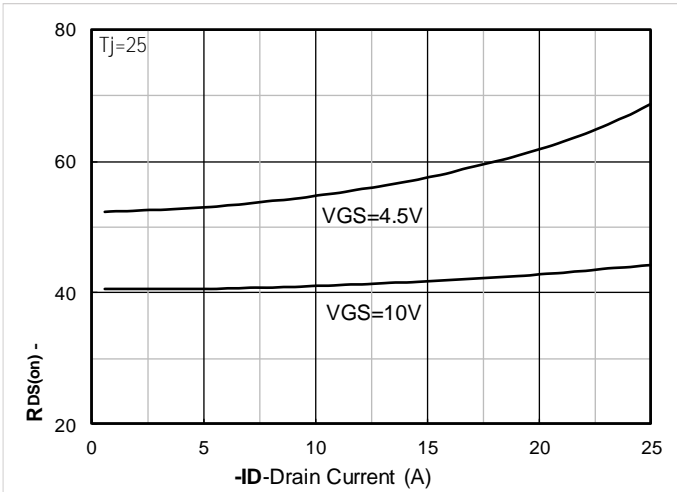


Figure 7. RDS(on) VS Drain Current

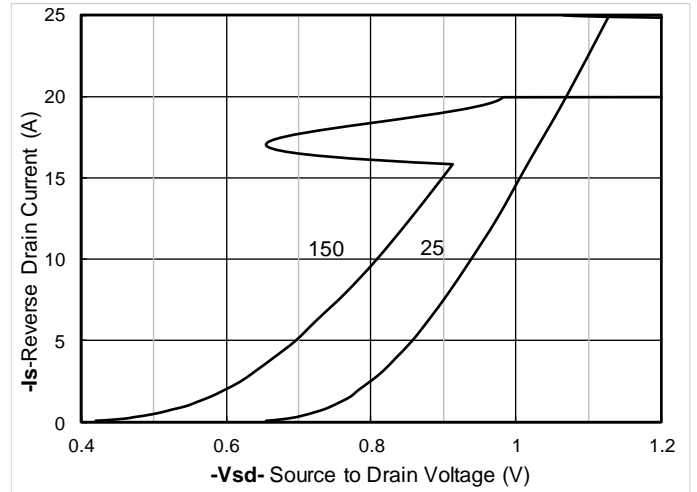


Figure 8. Forward characteristics of reverse diode

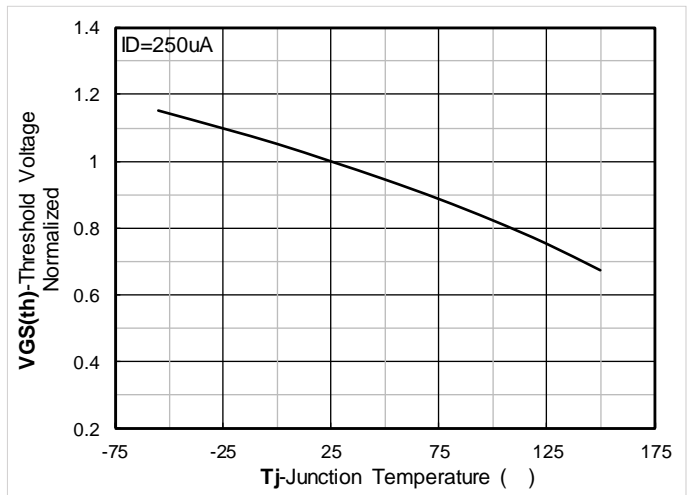
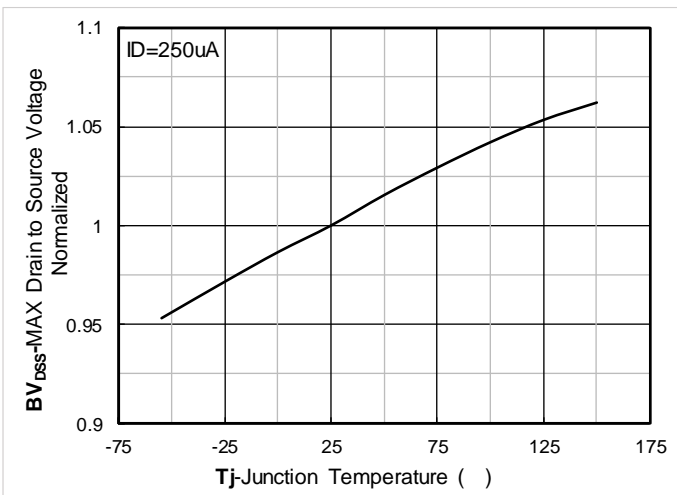


Figure 9. Normalized



13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area



SOT-223 Package Information



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